NSN 5962-01-352-7076

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Body Length:



View Online at https://aerobasegroup.com/nsn/5962-01-352-7076

0.540 inches	
Body Width:	
Between 0.245 inches and 0.300 inches	
Body Height:	
Between 0.045 inches and 0.100 inches	
Maximum Power Dissipation Rating:	
600.0 milliwatts	
Operating Tempurature Range:	
-55.0/+125.0 degrees celsius	
Storage Tempurature Range:	
-65.0/+150.0 degrees celsius	
Features Provided:	
Hermetically sealed and burn in and monolithic and electrostatic sensitive	
Inclosure Material:	
Ceramic	
Inclosure Configuration:	
Flat pack	
Output Logic Form:	
Transistor-transistor logic	
Input Circuit Pattern:	
16 input	
Case Outline Source And Designator:	
F-9 mil-m-38510	
Current Rating Per Characteristic:	
105.00 milliamperes reverse current, dc absolute	
Terminal Surface Treatment:	
Solder	
Product Name:	
And-or invert gate array	
Voltage Rating And Type Per Characteristic:	
-0.5 volts power source and 7.0 volts power source	
Time Rating Per Chacteristic:	
30.00 nanoseconds delay	
Memory Device Type:	
Pal	
Special Features:	
Nuclear hardness critical items	
Nuclear Hardness Critical Feature:	
Hardened	
Test Data Document:	
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, e	etc.).

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Terminal Type Aı	nd Quantity:
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20 flat leads

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0